

RMLV0816BGSB - 4S2

8Mb Advanced LPSRAM (512k word × 16bit)

R10DS0231EJ0201
Rev.2.01
2020.02.20

Description

The RMLV0816BGSB is a family of 8-Mbit static RAMs organized 524,288-word × 16-bit, fabricated by Renesas's high-performance Advanced LPSRAM technologies. The RMLV0816BGSB has realized higher density, higher performance and low power consumption. The RMLV0816BGSB offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It is offered in 44pin TSOP (II).

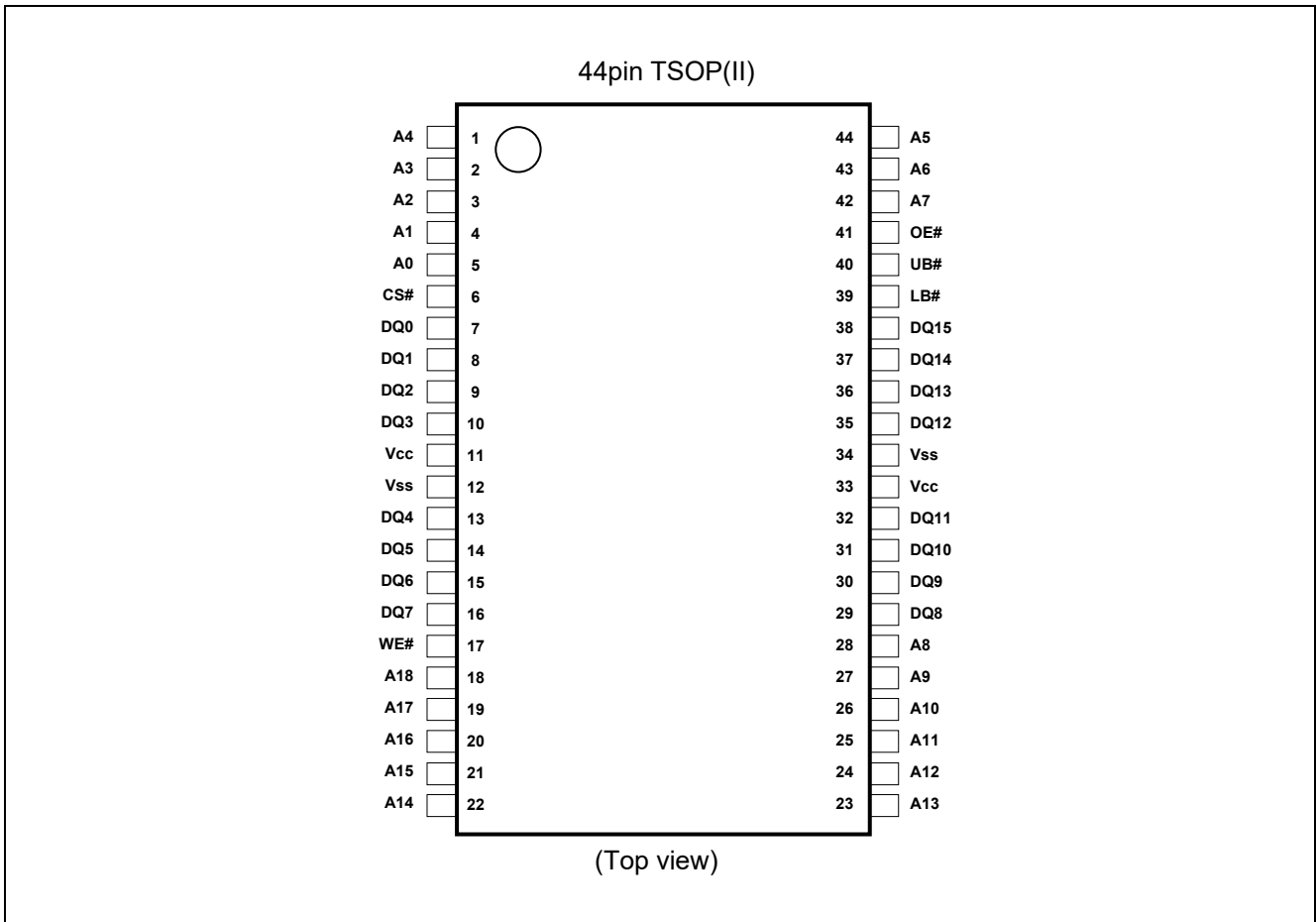
Features

- Single 3V supply: 2.4V to 3.6V
- Access time:
 - Power supply voltage from 2.7V to 3.6V: 45ns (max.)
 - Power supply voltage from 2.4V to 2.7V: 55ns (max.)
- Current consumption:
 - Standby: 0.45μA (typ.)
- Equal access and cycle times
- Common data input and output
 - Three state output
- Directly TTL compatible
 - All inputs and outputs
- Battery backup operation

Part Name Information

| Part Name | Power supply | Access time | Temperature Range | Package |
|------------------|--------------|-------------|-------------------|--|
| RMLV0816BGSB-4S2 | 2.7V to 3.6V | 45 ns | -40 ~ +85°C | 11.76mm×18.41mm 44pin plastic TSOP(II) |
| | 2.4V to 2.7V | 55 ns | | |

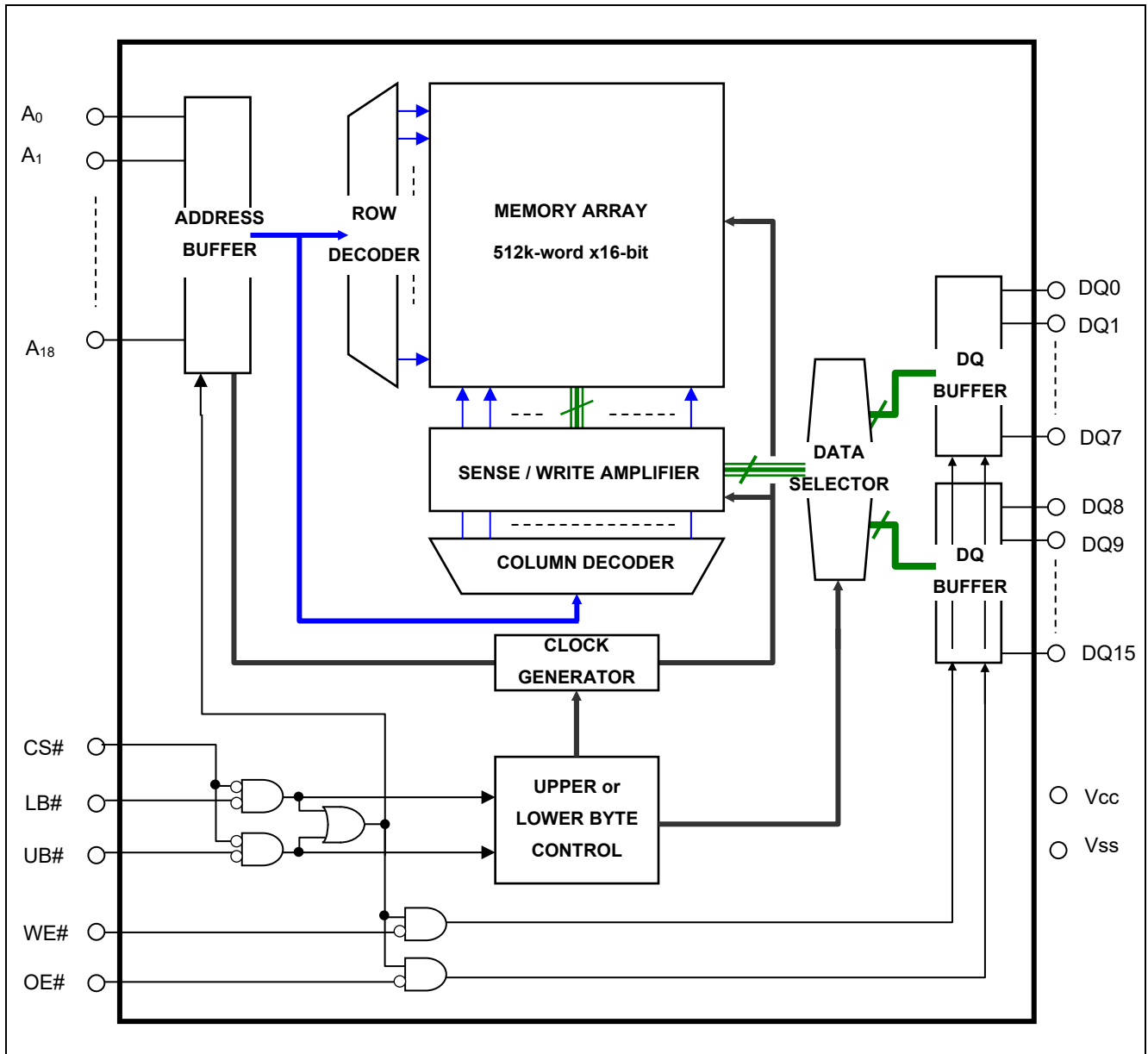
Pin Arrangement



Pin Description

| Pin name | Function |
|-----------------|-------------------|
| V _{CC} | Power supply |
| V _{SS} | Ground |
| A0 to A18 | Address input |
| DQ0 to DQ15 | Data input/output |
| CS# | Chip select |
| OE# | Output enable |
| WE# | Write enable |
| LB# | Lower byte select |
| UB# | Upper byte select |

Block Diagram



Operation Table

| CS# | WE# | OE# | UB# | LB# | DQ0 to DQ7 | DQ8 to DQ15 | Operation |
|-----|-----|-----|-----|-----|------------|-------------|------------------|
| H | X | X | X | X | High-Z | High-Z | Standby |
| X | X | X | H | H | High-Z | High-Z | Standby |
| L | H | L | L | L | Dout | Dout | Read |
| L | H | L | H | L | Dout | High-Z | Lower byte read |
| L | H | L | L | H | High-Z | Dout | Upper byte read |
| L | L | X | L | L | Din | Din | Write |
| L | L | X | H | L | Din | High-Z | Lower byte write |
| L | L | X | L | H | High-Z | Din | Upper byte write |
| L | H | H | X | X | High-Z | High-Z | Output disable |

Note 1. H: V_{IH} L: V_{IL} X: V_{IH} or V_{IL}

Absolute Maximum Ratings

| Parameter | Symbol | Value | unit |
|---|-------------------|--|------|
| Power supply voltage relative to V _{SS} | V _{CC} | -0.5 to +4.6 | V |
| Terminal voltage on any pin relative to V _{SS} | V _T | -0.5 ² to V _{CC} +0.3 ³ | V |
| Power dissipation | P _T | 0.7 | W |
| Operation temperature | T _{opr} | -40 to +85 | °C |
| Storage temperature range | T _{stg} | -65 to +150 | °C |
| Storage temperature range under bias | T _{bias} | -40 to +85 | °C |

Note 2. -3.0V for pulse ≤ 30ns (full width at half maximum)

3. Maximum voltage is +4.6V.

DC Operating Conditions

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test conditions | Note |
|---------------------------|-----------------|------|------|----------------------|------|-------------------------------|------|
| Supply voltage | V _{CC} | 2.4 | 3.0 | 3.6 | V | | |
| | V _{SS} | 0 | 0 | 0 | V | | |
| Input high voltage | V _{IH} | 2.0 | — | V _{CC} +0.2 | V | V _{CC} =2.4V to 2.7V | |
| | | 2.2 | — | V _{CC} +0.2 | V | V _{CC} =2.7V to 3.6V | |
| Input low voltage | V _{IL} | -0.2 | — | 0.4 | V | V _{CC} =2.4V to 2.7V | 4 |
| | | -0.2 | — | 0.6 | V | V _{CC} =2.7V to 3.6V | 4 |
| Ambient temperature range | T _a | -40 | — | +85 | °C | | |

Note 4. -3.0V for pulse ≤ 30ns (full width at half maximum)

DC Characteristics

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test conditions |
|---------------------------|------------------|------|--------------------|------|------|---|
| Input leakage current | I _{LI} | — | — | 1 | μA | V _{in} = V _{SS} to V _{CC} |
| Output leakage current | I _{LO} | — | — | 1 | μA | CS# = V _{IH} or OE# = V _{IH} or WE# = V _{IL} or LB# = UB# = V _{IH} , V _{I/O} = V _{SS} to V _{CC} |
| Average operating current | I _{CC1} | — | 20 ^{*5} | 25 | mA | Cycle = 55ns, duty = 100%, I _{I/O} = 0mA, CS# = V _{IL} , Others = V _{IH} /V _{IL} |
| | | — | 25 ^{*5} | 30 | mA | Cycle = 45ns, duty = 100%, I _{I/O} = 0mA, CS# = V _{IL} , Others = V _{IH} /V _{IL} |
| | I _{CC2} | — | 1.5 ^{*5} | 3 | mA | Cycle = 1μs, duty = 100%, I _{I/O} = 0mA CS# ≤ 0.2V, V _{IH} ≥ V _{CC} -0.2V, V _{IL} ≤ 0.2V |
| Standby current | I _{SB} | — | — | 0.3 | mA | CS# = V _{IH} , Others = V _{SS} to V _{CC} |
| Standby current | I _{SB1} | — | 0.45 ^{*5} | 2 | μA | ~+25°C |
| | | — | 0.6 ^{*6} | 4 | μA | ~+40°C |
| | | — | — | 7 | μA | ~+70°C |
| | | — | — | 10 | μA | ~+85°C |
| Output high voltage | V _{OH} | 2.4 | — | — | V | I _{OH} = -1mA V _{CC} ≥ 2.7V |
| | V _{OH2} | 2.0 | — | — | V | I _{OH} = -0.1mA |
| Output low voltage | V _{OL} | — | — | 0.4 | V | I _{OL} = 2mA V _{CC} ≥ 2.7V |
| | V _{OL2} | — | — | 0.4 | V | I _{OL} = 0.1mA |

Note 5. Typical parameter indicates the value for the center of distribution at 3.0V (T_a=25°C), and not 100% tested.

Note 6. Typical parameter indicates the value for the center of distribution at 3.0V (T_a=40°C), and not 100% tested.

Capacitance

(Ta =25°C, f =1MHz)

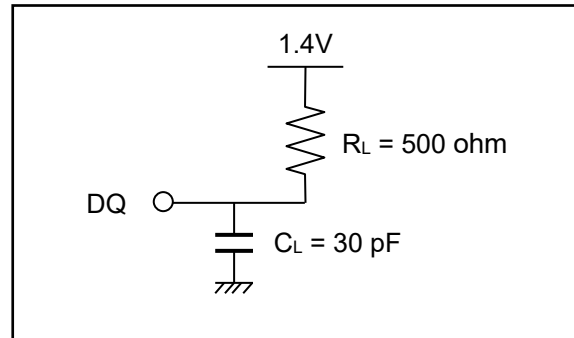
| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test conditions | Note |
|----------------------------|------------------|------|------|------|------|----------------------|------|
| Input capacitance | C _{in} | — | — | 8 | pF | V _{in} =0V | 7 |
| Input / output capacitance | C _{I/O} | — | — | 10 | pF | V _{I/O} =0V | 7 |

Note 7. This parameter is sampled and not 100% tested.

AC Characteristics

Test Conditions (V_{cc} = 2.4V ~ 3.6V, Ta = -40 ~ +85°C)

- Input pulse levels:
 - V_{IL} = 0.4V, V_{IH} = 2.4V (V_{cc}=2.7V to 3.6V)
 - V_{IL} = 0.4V, V_{IH} = 2.2V (V_{cc}=2.4V to 2.7V)
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.4V
- Output load: See figures (Including scope and jig)



Read Cycle

| Parameter | Symbol | V _{cc} =2.7V to 3.6V | | V _{cc} =2.4V to 2.7V | | Unit | Note |
|------------------------------------|-------------------|-------------------------------|------|-------------------------------|------|------|--------|
| | | Min. | Max. | Min. | Max. | | |
| Read cycle time | t _{RC} | 45 | — | 55 | — | ns | |
| Address access time | t _{AA} | — | 45 | — | 55 | ns | |
| Chip select access time | t _{ACS} | — | 45 | — | 55 | ns | |
| Output enable to output valid | t _{OE} | — | 22 | — | 30 | ns | |
| Output hold from address change | t _{OH} | 10 | — | 10 | — | ns | |
| LB#, UB# access time | t _{BA} | — | 45 | — | 55 | ns | |
| Chip select to output in low-Z | t _{C LZ} | 10 | — | 10 | — | ns | 8,9 |
| LB#, UB# enable to low-Z | t _{B LZ} | 5 | — | 5 | — | ns | 8,9 |
| Output enable to output in low-Z | t _{O LZ} | 5 | — | 5 | — | ns | 8,9 |
| Chip deselect to output in high-Z | t _{CHZ} | 0 | 18 | 0 | 20 | ns | 8,9,10 |
| LB#, UB# disable to high-Z | t _{BHZ} | 0 | 18 | 0 | 20 | ns | 8,9,10 |
| Output disable to output in high-Z | t _{O HZ} | 0 | 18 | 0 | 20 | ns | 8,9,10 |

Note 8. This parameter is sampled and not 100% tested.

- At any given temperature and voltage condition, t_{CHZ} max is less than t_{C LZ} min, t_{BHZ} max is less than t_{B LZ} min, and t_{O HZ} max is less than t_{O LZ} min, for any device.
- t_{CHZ}, t_{BHZ} and t_{O HZ} are defined as the time when the DQ pins enter a high-impedance state and are not referred to the DQ levels.

Write Cycle

| Parameter | Symbol | Vcc=2.7V to 3.6V | | Vcc=2.4V to 2.7V | | Unit | Note |
|------------------------------------|------------------|------------------|------|------------------|------|------|-------|
| | | Min. | Max. | Min. | Max. | | |
| Write cycle time | t _{WC} | 45 | — | 55 | — | ns | |
| Address valid to write end | t _{AW} | 35 | — | 50 | — | ns | |
| Chip select to write end | t _{CW} | 35 | — | 50 | — | ns | |
| Write pulse width | t _{WP} | 35 | — | 40 | — | ns | 11 |
| LB#,UB# valid to write end | t _{BW} | 35 | — | 50 | — | ns | |
| Address setup time to write start | t _{AS} | 0 | — | 0 | — | ns | |
| Write recovery time from write end | t _{WR} | 0 | — | 0 | — | ns | |
| Data to write time overlap | t _{DW} | 25 | — | 25 | — | ns | |
| Data hold from write end | t _{DH} | 0 | — | 0 | — | ns | |
| Output enable from write end | t _{OW} | 5 | — | 5 | — | ns | 12 |
| Output disable to output in high-Z | t _{OHZ} | 0 | 18 | 0 | 20 | ns | 12,13 |
| Write to output in high-Z | t _{WHZ} | 0 | 18 | 0 | 20 | ns | 12,13 |

Note 11. t_{WP} is the interval between write start and write end.

A write starts when all of (CS#), (WE#) and (one or both of LB# and UB#) become active.

A write is performed during the overlap of a low CS#, a low WE# and a low LB# or a low UB#.

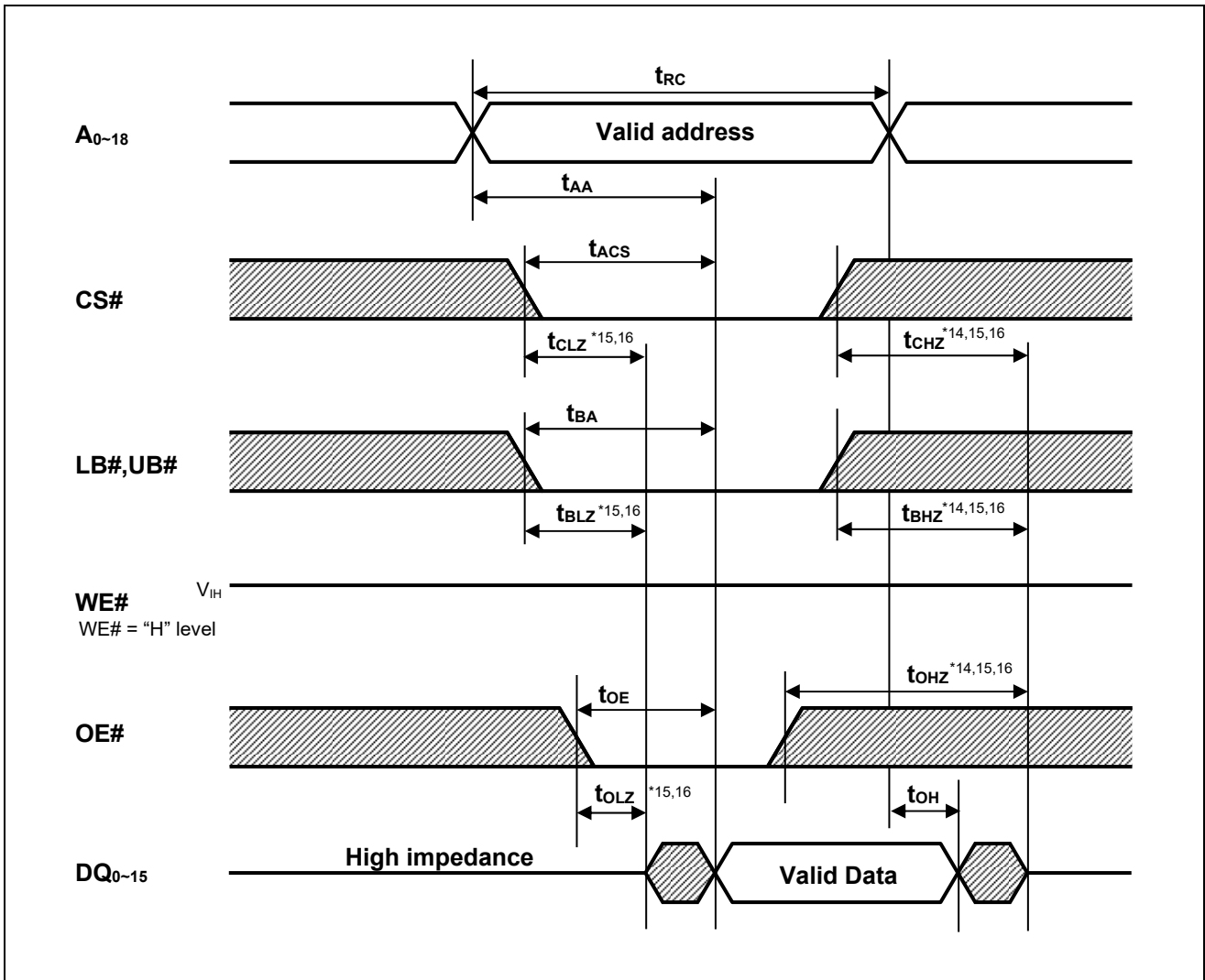
A write ends when any of (CS#), (WE#) or (one or both of LB# and UB#) becomes inactive.

12. This parameter is sampled and not 100% tested.

13. t_{OHZ} and t_{WHZ} are defined as the time when the DQ pins enter a high-impedance state and are not referred to the DQ levels.

Timing Waveforms

Read Cycle

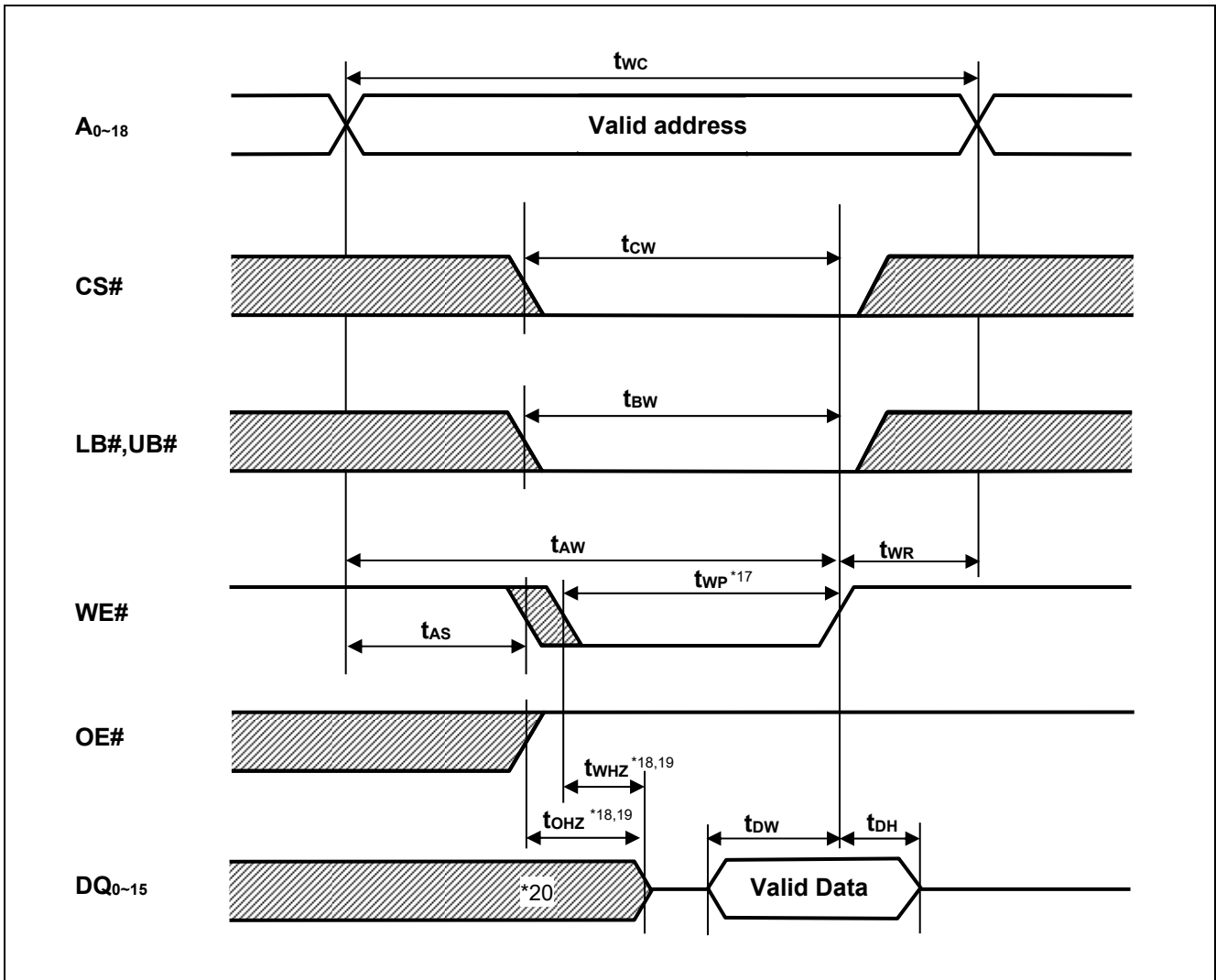


Note 14. t_{CHZ} , t_{BHZ} and t_{OHZ} are defined as the time when the DQ pins enter a high-impedance state and are not referred to the DQ levels.

15. This parameter is sampled and not 100% tested

16. At any given temperature and voltage condition, t_{CHZ} max is less than t_{CLZ} min, t_{BHZ} max is less than t_{BLZ} min, and t_{OHZ} max is less than t_{OLZ} min, for any device.

Write Cycle (1) (WE# CLOCK, OE#="H" while writing)



Note 17. t_{WP} is the interval between write start and write end.

A write starts when all of (CS#), (WE#) and (one or both of LB# and UB#) become active.

A write is performed during the overlap of a low CS#, a low WE# and a low LB# or a low UB#.

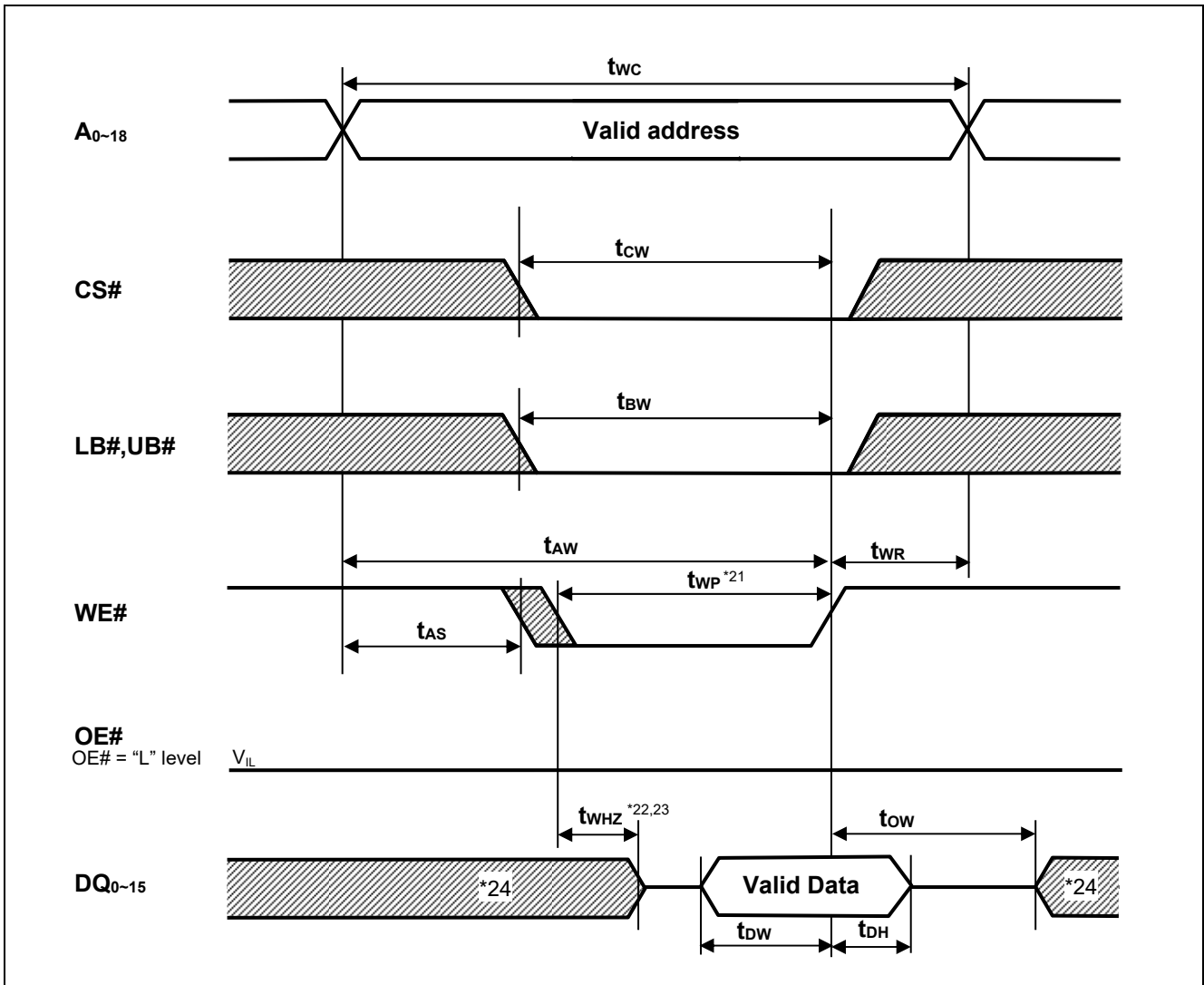
A write ends when any of (CS#), (WE#) or (one or both of LB# and UB#) becomes inactive.

18. t_{OHZ} and t_{WHZ} are defined as the time when the DQ pins enter a high-impedance state and are not referred to the DQ levels.

19. This parameter is sampled and not 100% tested

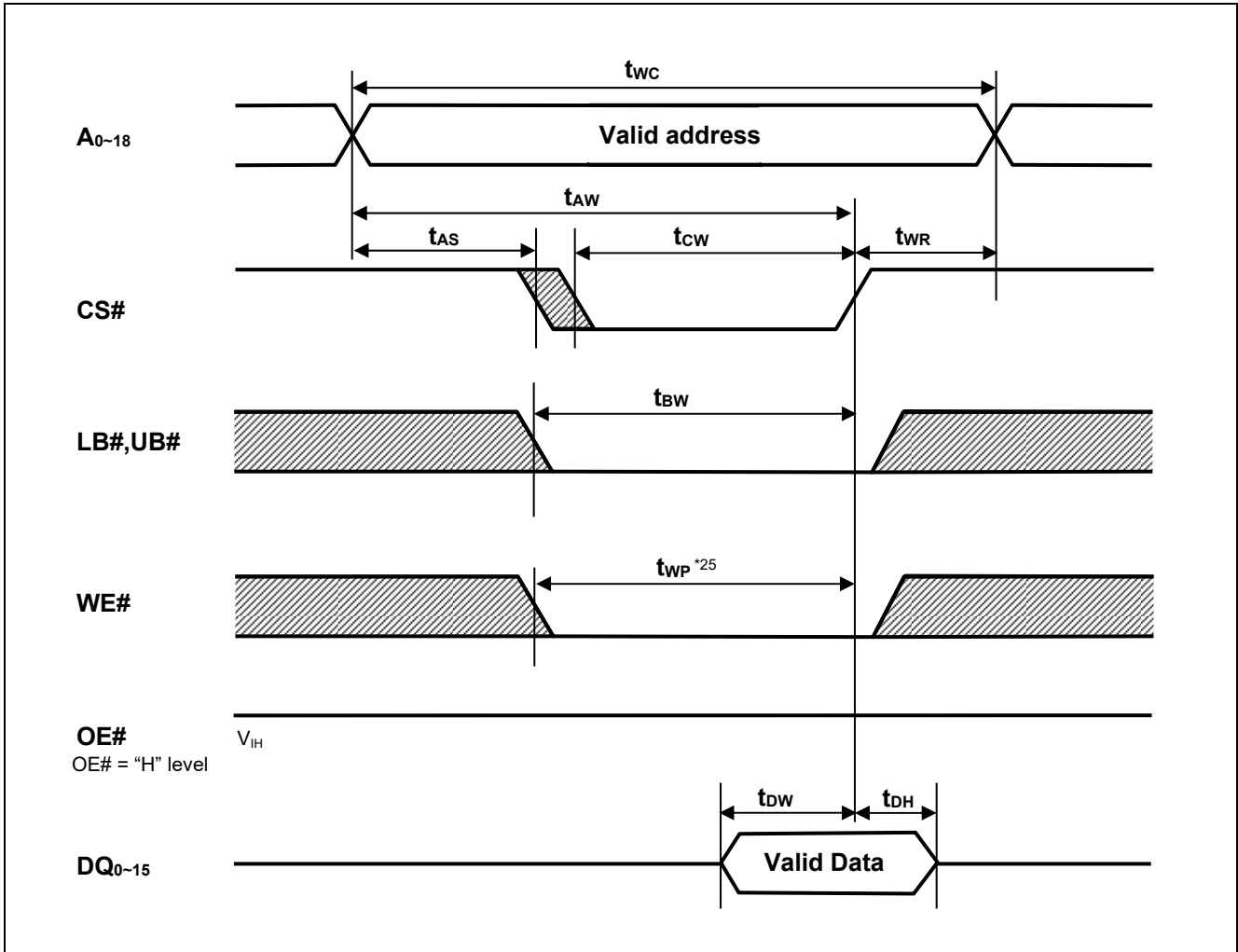
20. During this period, DQ pins are in the output state so input signals must not be applied to the DQ pins.

Write Cycle (2) (WE# CLOCK, OE# Low Fixed)



- Note 21. t_{WP} is the interval between write start and write end.
 A write starts when all of (CS#), (WE#) and (one or both of LB# and UB#) become active.
 A write is performed during the overlap of a low CS#, a low WE# and a low LB# or a low UB#.
 A write ends when any of (CS#), (WE#) or (one or both of LB# and UB#) becomes inactive.
22. t_{WHZ} is defined as the time when the DQ pins enter a high-impedance state and are not referred to the DQ levels.
23. This parameter is sampled and not 100% tested.
24. During this period, DQ pins are in the output state so input signals must not be applied to the DQ pins.

Write Cycle (3) (CS# CLOCK)



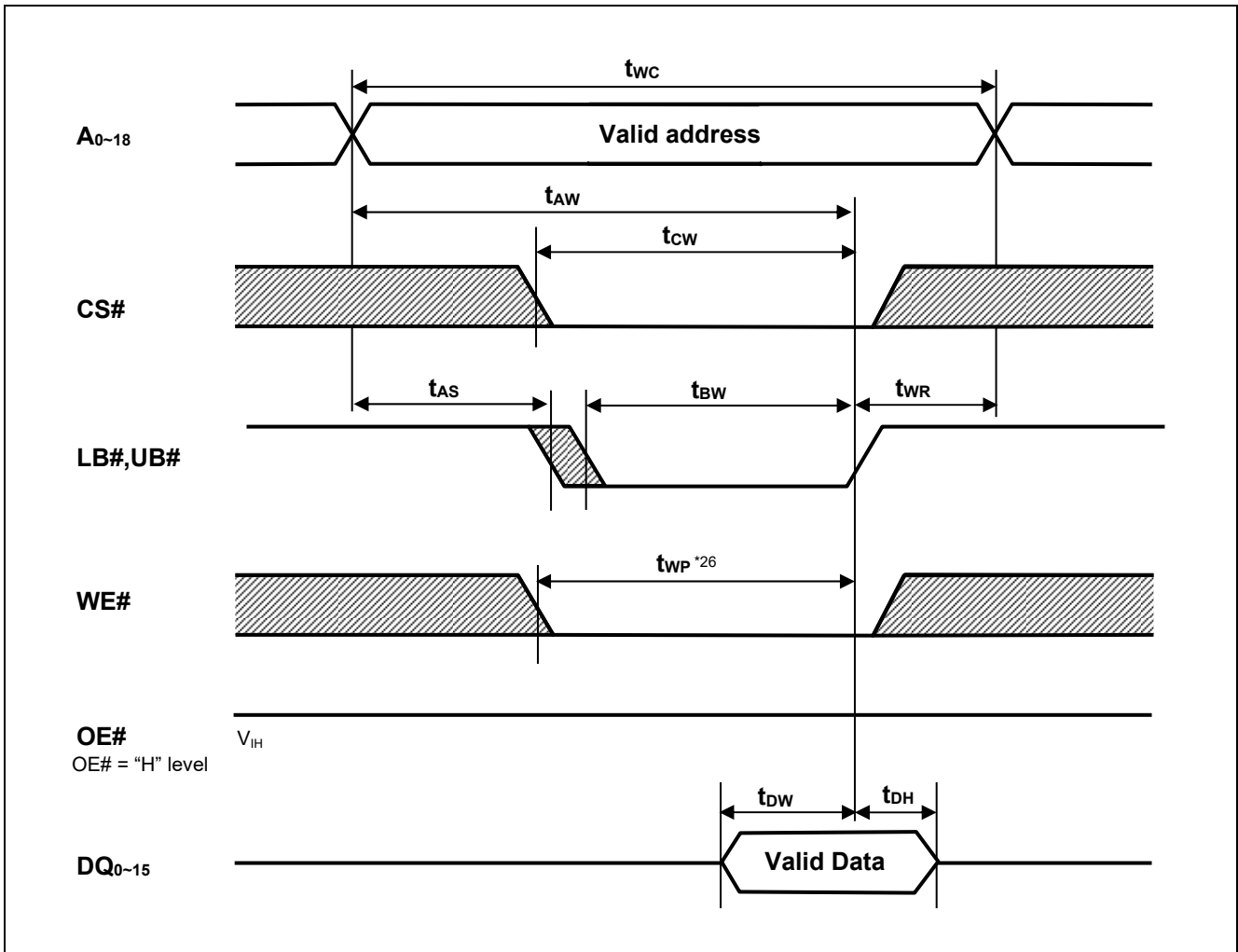
Note 25. t_{WP} is the interval between write start and write end.

A write starts when all of (CS#), (WE#) and (one or both of LB# and UB#) become active.

A write is performed during the overlap of a low CS#, a low WE# and a low LB# or a low UB#.

A write ends when any of (CS#), (WE#) or (one or both of LB# and UB#) becomes inactive.

Write Cycle (4) (LB#, UB# CLOCK)



Note 26. t_{WP} is the interval between write start and write end.

A write starts when all of (CS#), (WE#) and (one or both of LB# and UB#) become active.

A write is performed during the overlap of a low CS#, a low WE# and a low LB# or a low UB#.

A write ends when any of (CS#), (WE#) or (one or both of LB# and UB#) becomes inactive.

Low V_{CC} Data Retention Characteristics

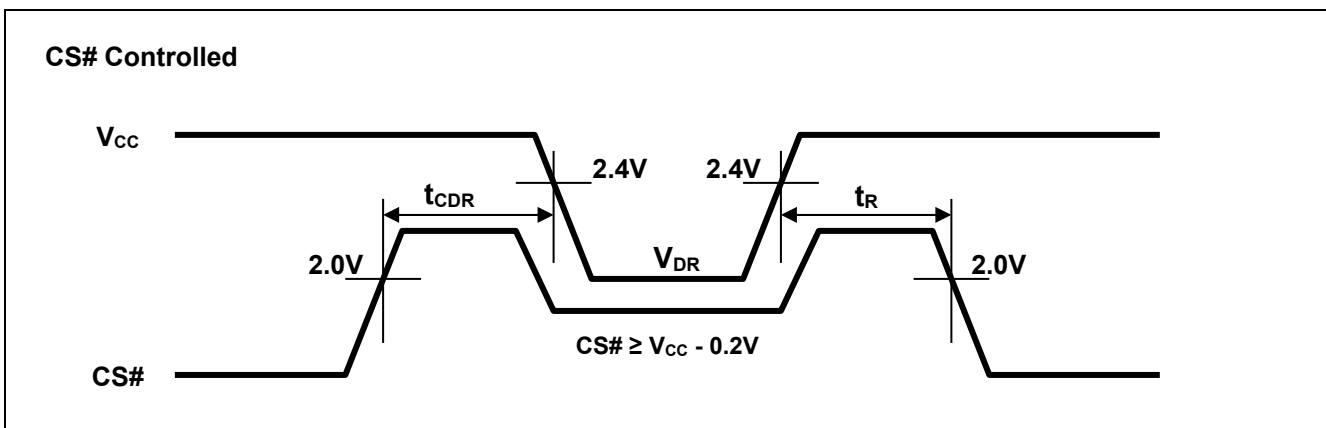
| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test conditions ^{*29} | |
|--------------------------------------|-------------------|------|---------------------|------|------|---|--|
| V _{CC} for data retention | V _{DR} | 1.5 | — | 3.6 | V | V _{in} ≥ 0V, (1) CS# ≥ V _{CC} -0.2V or (2) LB# = UB# ≥ V _{CC} -0.2V, CS# ≤ 0.2V | |
| Data retention current | I _{CCDR} | — | 0.45 ^{*27} | 2 | μA | ~+25°C | V _{CC} =3.0V, V _{in} ≥ 0V, (1) CS# ≥ V _{CC} -0.2V or (2) LB# = UB# ≥ V _{CC} -0.2V, CS# ≤ 0.2V |
| | | — | 0.6 ^{*28} | 4 | μA | ~+40°C | |
| | | — | — | 7 | μA | ~+70°C | |
| | | — | — | 10 | μA | ~+85°C | |
| Chip deselect time to data retention | t _{CDR} | 0 | — | — | ns | See retention waveform. | |
| Operation recovery time | t _R | 5 | — | — | ms | | |

Note 27. Typical parameter indicates the value for the center of distribution at 3.0V (T_a=25°C), and not 100% tested.

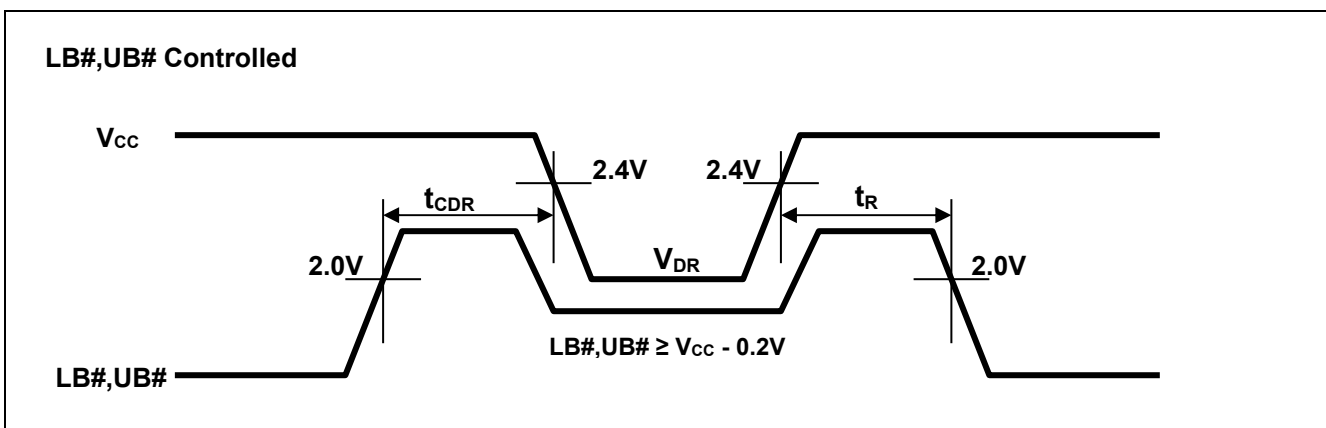
28. Typical parameter indicates the value for the center of distribution at 3.0V (T_a=40°C), and not 100% tested.

29. CS# controls address buffer, WE# buffer, OE# buffer, LB# buffer, UB# buffer and DQ buffer. If CS# controls data retention mode, V_{in} levels (address, WE#, OE#, LB#, UB#, DQ) can be in the high impedance state.

Low V_{CC} Data Retention Timing Waveforms (CS# controlled)



Low V_{CC} Data Retention Timing Waveforms (LB#,UB# controlled)



| | |
|------------------|-------------------------|
| Revision History | RMLV0816BGSB Data Sheet |
|------------------|-------------------------|

| Rev. | Date | Description | |
|------|------------|------------------------------|---|
| | | Page | Summary |
| 1.00 | 2014.11.28 | — | First Edition issued |
| 2.00 | 2015.06.26 | P.1, 4 P.2 P.4 P.12 | Standby current I_{SB1} : 25°C 0.6μA ->0.45μA (typ.), 40°C 2μA ->0.6μA (typ.) Modify Pin Arrangement : Add 1pin Mark Average operating current I_{CC2} : 25°C 2mA ->1.5mA (typ.) Data retention current I_{CCDR} : 25°C 0.6μA ->0.45μA (typ.), 40°C 2μA ->0.6μA (typ.) |
| 2.01 | 2020.02.20 | Last page | Updated the Notice to the latest version |
| | | | |

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